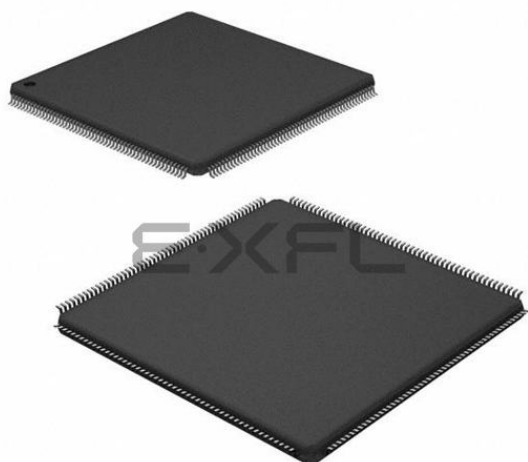




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Details

Product Status	Active
Core Processor	ARM® Cortex® -M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SAI, SPDIF, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	159
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f769bgt6

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Table 2. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx features and peripheral counts

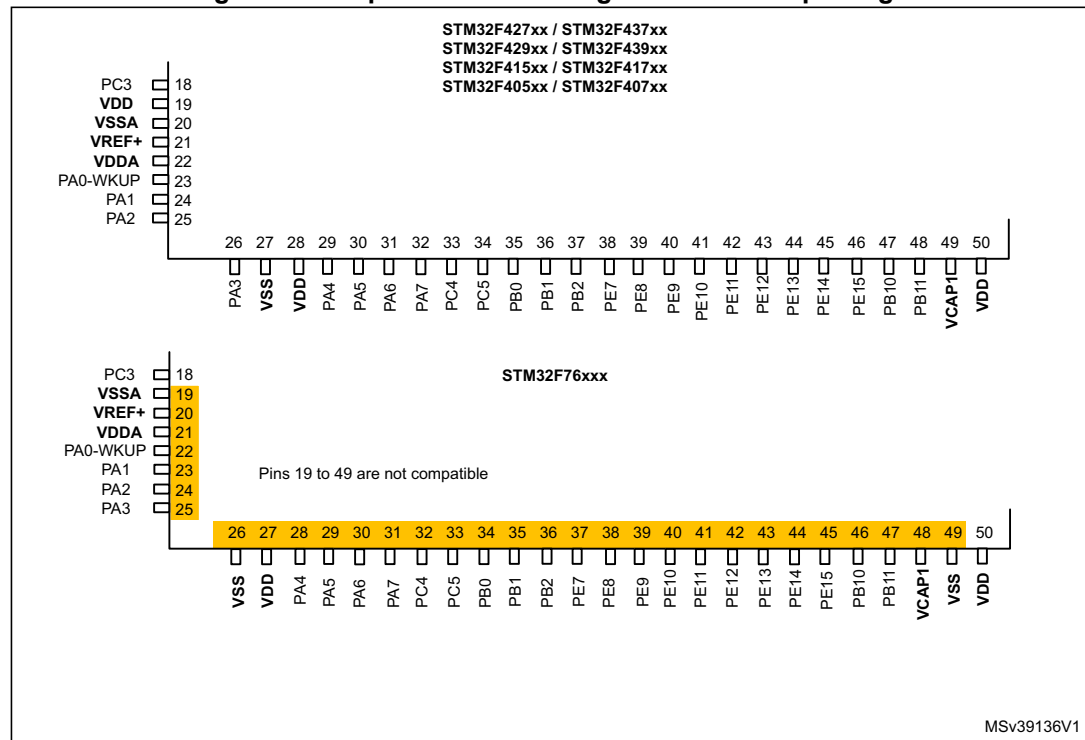
Peripherals		STM32F765Vx		STM32F767/769Vx		STM32F765Zx		STM32F767/769Zx		STM32F769Ax		STM32F768Ax		STM32F765Ix		STM32F767/769Ix		STM32F765Bx		STM32F767/769Bx		STM32F765Nx		STM32F767/769Nx	
Flash memory in Kbytes		1024	2048	1024	2048	1024	2048	1024	2048	1024	2048	2048		1024	2048	1024	2048	1024	2048	1024	2048	1024	2048	1024	2048
SRAM in Kbytes	System	512(368+16+128)																							
	Instruction	16																							
	Backup	4																							
FMC memory controller		Yes ⁽¹⁾																							
Quad-SPI		Yes																							
Ethernet		Yes								No				Yes											
Timers	General-purpose	10																							
	Advanced-control	2																							
	Basic	2																							
	Low-power	1																							
Random number generator		Yes																							
Communication interfaces	SPI / I ² S	4/3 (simplex) ⁽²⁾				6/3 (simplex) ⁽²⁾																			
	I ² C	4																							
	USART/UART	4/4																							
	USB OTG FS	Yes																							
	USB OTG HS	Yes																							
	CAN	3																							
	SAI	2																							
	SPDIFRX	4 inputs																							
	SDMMC1	Yes																							
	SDMMC2	Yes ⁽³⁾																							
Camera interface		Yes																							
MIPI-DSI Host ⁽⁴⁾		No								Yes				No		Yes		No		Yes		No		Yes	
LCD-TFT		No		Yes		No		Yes				No		Yes		No		Yes		No		Yes			

1.1 Full compatibility throughout the family

The STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx devices are fully pin-to-pin, compatible with the STM32F4xxxx devices, allowing the user to try different peripherals, and reaching higher performances (higher frequency) for a greater degree of freedom during the development cycle.

Figure 1 gives compatible board designs between the STM32F7xx and STM32F4xx families.

Figure 1. Compatible board design for LQFP100 package



The STM32F76x LQFP144, LQFP176, LQFP208, TFBGA216, UFBGA176 packages are fully pin to pin compatible with STM32F4xx devices.

2.31 SD/SDIO/MMC card host interface (SDMMC)

SDMMC host interfaces are available, that support the MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 50 MHz, and is compliant with the SD Memory Card Specification Version 2.0.

The SDMMC Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDMMC/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

The SDMMC can be served by the DMA controller

2.32 Ethernet MAC interface with dedicated DMA and IEEE 1588 support

The devices provide an IEEE-802.3-2002-compliant media access controller (MAC) for ethernet LAN communications through an industry-standard medium-independent interface (MII) or a reduced medium-independent interface (RMII). The microcontroller requires an external physical interface device (PHY) to connect to the physical LAN bus (twisted-pair, fiber, etc.). The PHY is connected to the device MII port using 17 signals for MII or 9 signals for RMII, and can be clocked using the 25 MHz (MII) from the microcontroller.

The devices include the following features:

- Supports 10 and 100 Mbit/s rates
- Dedicated DMA controller allowing high-speed transfers between the dedicated SRAM and the descriptors
- Tagged MAC frame support (VLAN support)
- Half-duplex (CSMA/CD) and full-duplex operation
- MAC control sublayer (control frames) support
- 32-bit CRC generation and removal
- Several address filtering modes for physical and multicast address (multicast and group addresses)
- 32-bit status code for each transmitted or received frame
- Internal FIFOs to buffer transmit and receive frames. The transmit FIFO and the receive FIFO are both 2 Kbytes.
- Supports hardware PTP (precision time protocol) in accordance with IEEE 1588 2008 (PTP V2) with the time stamp comparator connected to the TIM2 input
- Triggers interrupt when system time becomes greater than target time

Table 10. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F765xx STM32F767xx						STM32F768Ax STM32F769xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180 ⁽¹⁾	LQFP176	LQFP208	TFBGA216						
-	19	K1	25	28	K1	NC	25	28	K1	PF7	I/O	FT	-	TIM11_CH1, SPI5_SCK, SAI1_MCLK_B, UART7_TX, QUADSPI_BK1_IO2, EVENTOUT	ADC3_IN5
-	20	L3	26	29	L3	NC	26	29	L3	PF8	I/O	FT	-	SPI5_MISO, SAI1_SCK_B, UART7_RTS, TIM13_CH1, QUADSPI_BK1_IO0, EVENTOUT	ADC3_IN6
-	21	L2	27	30	L2	NC	27	30	L2	PF9	I/O	FT	-	SPI5_MOSI, SAI1_FS_B, UART7_CTS, TIM14_CH1, QUADSPI_BK1_IO1, EVENTOUT	ADC3_IN7
-	22	L1	28	31	L1	K11	28	31	L1	PF10	I/O	FT	-	QUADSPI_CLK, DCMI_D11, LCD_DE, EVENTOUT	ADC3_IN8
12	23	G1	29	32	G1	K12	29	32	G1	PH0-OSC_IN	I/O	FT	(3)	EVENTOUT	OSC_IN
13	24	H1	30	33	H1	K13	30	33	H1	PH1-OSC_OUT	I/O	FT	(3)	EVENTOUT	OSC_OUT
14	25	J1	31	34	J1	L11	31	34	J1	NRST	I/O	RS T	-	-	-
15	26	M2	32	35	M2	L12	32	35	M2	PC0	I/O	FT	-	DFSDM1_CKIN0, DFSDM1_DATIN4, SAI2_FS_B, OTG_HS_ULPI_STP, FMC_SDNWE, LCD_R5, EVENTOUT	ADC1_IN10, ADC2_IN10, ADC3_IN10
16	27	M3	33	36	M3	L13	33	36	M3	PC1	I/O	FT	-	TRACED0, DFSDM1_DATIN0, SPI2_MOSI/I2S2_SD, SAI1_SD_A, DFSDM1_CKIN4, ETH_MDC, MDIOS_MDC, EVENTOUT	ADC1_IN11, ADC2_IN11, ADC3_IN11, RTC_TAMP3/WKUP3

Table 10. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx pin and ball definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F765xx STM32F767xx						STM32F768Ax STM32F769xx									
LQFP100	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216	WLCSP180 ⁽¹⁾	LQFP176	LQFP208	TFBGA216						
-	128	A8	156	182	B3	C7	156	182	B3	PG13	I/O	FT	-	TRACED0, LPTIM1_OUT, SPI6_SCK, USART6_CTS, ETH_MII_TXD0/ETH_RMII_TXD0, FMC_A24, LCD_R0, EVENTOUT	-
-	129	A7	157	183	A4	NC	157	183	A4	PG14	I/O	FT	-	TRACED1, LPTIM1_ETR, SPI6_MOSI, USART6_TX, QUADSPI_BK2_IO3, ETH_MII_TXD1/ETH_RMII_TXD1, FMC_A25, LCD_B0, EVENTOUT	-
-	130	D7	158	184	F7	A8	158	184	F7	VSS	S	-	-	-	-
-	131	C7	159	185	E8	B8	159	185	E8	VDD	S	-	-	-	-
-	-	-	-	186	D8	NC	-	186	D8	PK3	I/O	FT	-	LCD_B4, EVENTOUT	-
-	-	-	-	187	D7	NC	-	187	D7	PK4	I/O	FT	-	LCD_B5, EVENTOUT	-
-	-	-	-	188	C6	NC	-	188	C6	PK5	I/O	FT	-	LCD_B6, EVENTOUT	-
-	-	-	-	189	C5	NC	-	189	C5	PK6	I/O	FT	-	LCD_B7, EVENTOUT	-
-	-	-	-	190	C4	NC	-	190	C4	PK7	I/O	FT	-	LCD_DE, EVENTOUT	-
-	132	B7	160	191	B7	F9	160	191	B7	PG15	I/O	FT	-	USART6_CTS, FMC_SDNCAS, DCMI_D13, EVENTOUT	-
89	133	A10	161	192	A10	E8	161	192	A10	PB3 (JTDO/TRACESWO)	I/O	FT	-	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK/I2S1_CK, SPI3_SCK/I2S3_CK, SPI6_SCK, SDMMC2_D2, CAN3_RX, UART7_RX, EVENTOUT	-
90	134	A9	162	193	A9	D8	162	193	A9	PB4(NJT RST)	I/O	FT	-	NJTRST, TIM3_CH1, SPI1_MISO, SPI3_MISO, SPI2_NSS/I2S2_WS, SPI6_MISO, SDMMC2_D3, CAN3_TX, UART7_TX, EVENTOUT	-

Table 13. STM32F765xx, STM32F767xx, STM32F768Ax and STM32F769xx register boundary addresses⁽¹⁾ (continued)

Bus	Boundary address	Peripheral
	0x4000 8000 - 0x4000 FFFF	Reserved
APB1	0x4000 7C00 - 0x4000 7FFF	UART8
	0x4000 7800 - 0x4000 7BFF	UART7
	0x4000 7400 - 0x4000 77FF	DAC
	0x4000 7000 - 0x4000 73FF	PWR
	0x4000 6C00 - 0x4000 6FFF	HDMI-CEC
	0x4000 6800 - 0x4000 6BFF	CAN2
	0x4000 6400 - 0x4000 67FF	CAN1
	0x4000 6000 - 0x4000 63FF	I2C4
	0x4000 5C00 - 0x4000 5FFF	I2C3
	0x4000 5800 - 0x4000 5BFF	I2C2
	0x4000 5400 - 0x4000 57FF	I2C1
	0x4000 5000 - 0x4000 53FF	UART5
	0x4000 4C00 - 0x4000 4FFF	UART4
	0x4000 4800 - 0x4000 4BFF	USART3
	0x4000 4400 - 0x4000 47FF	USART2
	0x4000 4000 - 0x4000 43FF	SPDIFRX
	0x4000 3C00 - 0x4000 3FFF	SPI3 / I2S3
	0x4000 3800 - 0x4000 3BFF	SPI2 / I2S2
	0x4000 3400 - 0x4000 37FF	CAN3
	0x4000 3000 - 0x4000 33FF	IWDG
	0x4000 2C00 - 0x4000 2FFF	WWDG
	0x4000 2800 - 0x4000 2BFF	RTC & BKP Registers
	0x4000 2400 - 0x4000 27FF	LPTIM1
	0x4000 2000 - 0x4000 23FF	TIM14
	0x4000 1C00 - 0x4000 1FFF	TIM13
	0x4000 1800 - 0x4000 1BFF	TIM12
	0x4000 1400 - 0x4000 17FF	TIM7
	0x4000 1000 - 0x4000 13FF	TIM6
	0x4000 0C00 - 0x4000 0FFF	TIM5
	0x4000 0800 - 0x4000 0BFF	TIM4
	0x4000 0400 - 0x4000 07FF	TIM3
	0x4000 0000 - 0x4000 03FF	TIM2

1. The gray color is used for reserved Flash memory addresses.

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\sigma$).

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $1.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\sigma$).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 22](#).

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 23](#).

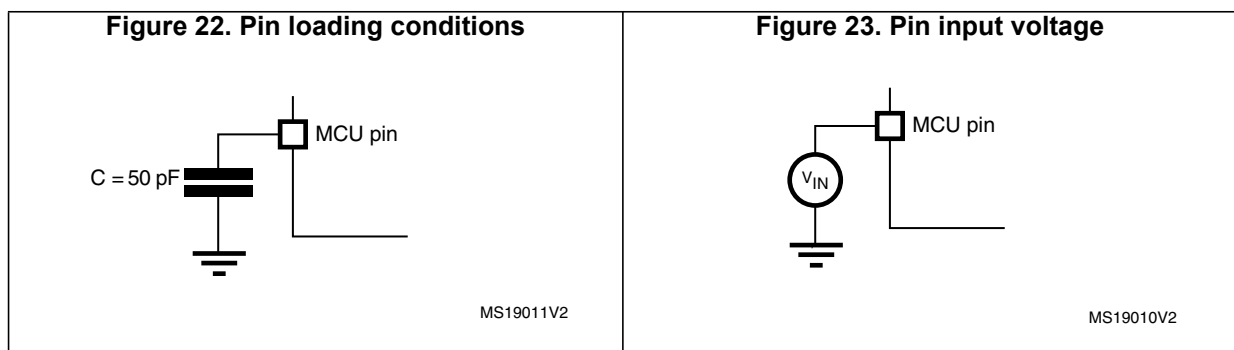


Table 17. General operating conditions (continued)

Symbol	Parameter	Conditions ⁽¹⁾	Min	Typ	Max	Unit
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 144 MHz HCLK max frequency	1.08	1.14	1.20	V
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON	1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 180 MHz HCLK max frequency with over-drive OFF or 216 MHz with over-drive ON	1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V_{CAP_1}/V_{CAP_2} pins ⁽⁷⁾	Max frequency 144 MHz	1.10	1.14	1.20	
		Max frequency 168MHz	1.20	1.26	1.32	
		Max frequency 180 MHz	1.26	1.32	1.38	
V_{IN}	Input voltage on RST and FT pins ⁽⁸⁾	$2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$	- 0.3	-	5.5	
		$V_{DD} \leq 2\text{ V}$	- 0.3	-	5.2	
	Input voltage on TTa pins	-	- 0.3	-	$V_{DDA} + 0.3$	
	Input voltage on BOOT pin	-	0	-	9	
P_D	Power dissipation at $T_A = 85\text{ °C}$ for suffix 6 or $T_A = 105\text{ °C}$ for suffix 7 ⁽⁹⁾	LQFP100	-	-	465	mW
		WLCSP180	-	-	641	
		LQFP144	-	-	500	
		LQFP176	-	-	526	
		UFBGA176	-	-	513	
		LQFP208	-	-	1053	
		TFBGA216	-	-	690	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	- 40	-	85	°C
		Low power dissipation ⁽¹⁰⁾	- 40	-	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	- 40	-	105	°C
		Low power dissipation ⁽¹⁰⁾	- 40	-	125	
T_J	Junction temperature range	6 suffix version	- 40	-	105	°C
		7 suffix version	- 40	-	125	

1. The over-drive mode is not supported at the voltage ranges from 1.7 to 2.1 V.
2. 216 MHz maximum frequency for 6 suffix version (200 MHz maximum frequency for 7 suffix version).
3. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to [Section 2.18.2: Internal reset OFF](#)).
4. When the ADC is used, refer to [Table 71: ADC characteristics](#).
5. If V_{REF+} pin is present, it must respect the following condition: $V_{DDA} - V_{REF+} < 1.2\text{ V}$.
6. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and power-down operation.

Table 28. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode), regulator ON

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					TA= 25 °C	TA=85 °C	TA=105 °C	
I _{DD}	Supply current in RUN mode	All peripherals enabled ⁽²⁾⁽³⁾	216	176	194	240	-	mA
			200	164	181	227	255	
			180	149	163	198	220	
			168	133	145	178	198	
			144	106	116	143	161	
			60	54	60	87	105	
			25	27	31	58	76	
		All peripherals disabled ⁽³⁾	216	77	88	135	-	
			200	72	82	129	157	
			180	67	75	110	131	
			168	60	67	99	120	
			144	50	56	83	101	
			60	29	34	60	78	
			25	15	19	45	63	

1. Guaranteed by characterization results, unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 31. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Single bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ		Max ⁽¹⁾						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and VDD supply	All Peripherals Enabled ⁽²⁾⁽³⁾	180	152	1	167	2	200	2	220	2	mA
			168	136	1	148	2	179	2	198	2	
			144	105	1	115	2	141	2	158	2	
			60	47	1	53	2	79	2	96	2	
			25	22	1	27	2	53	2	70	2	
		All Peripherals Disabled ⁽³⁾	180	74	1	83	2	116	2	136	2	
			168	65	1	73	2	104	2	123	2	
			144	50	1	57	2	83	2	100	2	
			60	22	1	27	2	53	2	70	2	
			25	10	1	14	2	41	2	58	2	

1. Guaranteed by characterization results.

2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.

3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Table 32. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (Dual bank mode, ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator OFF

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ		Max ⁽¹⁾						Unit
						TA= 25 °C		TA= 85 °C		TA= 105 °C		
				IDD12	IDD	IDD12	IDD	IDD12	IDD	IDD12	IDD	
IDD12/ IDD	Supply current in RUN mode from V12 and VDD supply	All Peripherals Enabled ⁽²⁾⁽³⁾	180	152	1	167	2	200	2	220	2	mA
			168	136	1	148	2	179	2	198	2	
			144	105	1	115	2	141	2	158	2	
			60	47	1	53	2	79	2	96	2	
			25	22	1	27	2	53	2	70	2	
		All Peripherals Disabled ⁽³⁾	180	74	1	82	2	114	2	137	2	
			168	65	1	73	2	104	2	123	2	
			144	50	1	57	2	83	2	100	2	
			60	22	1	27	2	53	2	70	2	
			25	10	1	14	2	41	2	58	2	

Table 36. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ ⁽¹⁾			Max ⁽²⁾			Unit
			T _A = 25 °C			T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
			V _{DD} = 1.7 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} = 3.3 V			
I _{DD_STBY}	Supply current in Standby mode	Backup SRAM OFF, RTC and LSE OFF	1.1	1.9	2.4	5 ⁽³⁾	18 ⁽³⁾	38 ⁽³⁾	µA
		Backup SRAM ON, RTC and LSE OFF	1.9	2.7	3.2	6 ⁽³⁾	23 ⁽³⁾	48 ⁽³⁾	
		Backup SRAM OFF, RTC ON and LSE in low drive mode	1.7	2.7	3.5	7	26	55	
		Backup SRAM OFF, RTC ON and LSE in medium low drive mode	1.7	2.7	3.5	7	26	56	
		Backup SRAM OFF, RTC ON and LSE in medium high drive mode	1.8	2.8	3.6	8	28	57	
		Backup SRAM OFF, RTC ON and LSE in high drive mode	1.9	2.9	3.7	8	28	59	
		Backup SRAM ON, RTC ON and LSE in low drive mode	2.4	3.4	4.3	8	31	65	
		Backup SRAM ON, RTC ON and LSE in Medium low drive mode	2.4	3.5	4.3	8	31	65	
		Backup SRAM ON, RTC ON and LSE in Medium high drive mode	2.6	3.7	4.5	8	33	68	
		Backup SRAM ON, RTC ON and LSE in High drive mode	2.6	3.7	4.5	9	33	68	

1. The typical current consumption values are given with PDR OFF (internal reset OFF). When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA.
2. Guaranteed by characterization results, unless otherwise specified.
3. Guaranteed by test in production.

5.3.8 Wakeup time from low-power modes

The wakeup times given in [Table 40](#) are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

All timings are derived from tests performed under ambient temperature and $V_{DD}=3.3$ V.

Table 40. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
$t_{WUSLEEP}^{(2)}$	Wakeup from Sleep	-	13	13	CPU clock cycles
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in normal mode	Main regulator is ON	14	14.9	μs
		Main regulator is ON and Flash memory in Deep power down mode	104.1	107.6	
		Low power regulator is ON	21.4	24.2	
		Low power regulator is ON and Flash memory in Deep power down mode	111.5	116.5	
$t_{WUSTOP}^{(2)}$	Wakeup from Stop mode with MR/LP regulator in Under-drive mode	Main regulator in under-drive mode (Flash memory in Deep power-down mode)	107.4	113.2	
		Low power regulator in under-drive mode (Flash memory in Deep power-down mode)	112.7	120	
$t_{WUSTDBY}^{(2)}$	Wakeup from Standby mode	Exit Standby mode on rising edge	308	313	
		Exit Standby mode on falling edge	307	313	

1. Guaranteed by characterization results.

2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

Figure 36. MIPI D-PHY HS/LP clock lane transition timing diagram

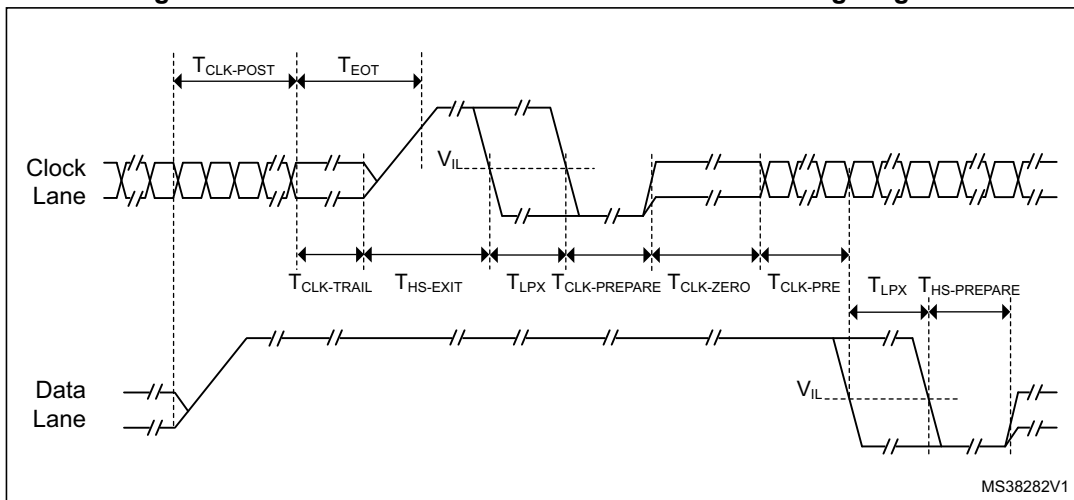
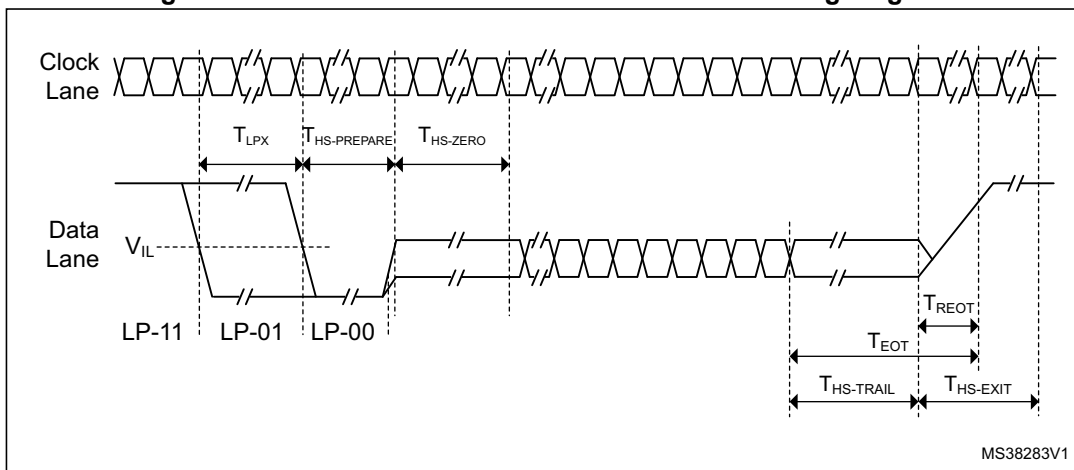


Figure 37. MIPI D-PHY HS/LP data lane transition timing diagram



5.3.14 MIPI D-PHY PLL characteristics

The parameters given in [Table 53](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 53. DSI-PLL characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock	-	4	-	100	MHz
f_{PLL_INFIN}	PFD input clock	-	4	-	25	
f_{PLL_OUT}	PLL multiplier output clock	-	31.25	-	500	
f_{VCO_OUT}	PLL VCO output	-	500	-	1000	
t_{LOCK}	PLL lock time	-	-	-	200	μs

Table 53. DSI-PLL characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{DD(PLL)}	PLL power consumption on V _{DD12}	f _{VCO_OUT} = 500 MHz	-	0.55	0.70	mA
		f _{VCO_OUT} = 600 MHz	-	0.65	0.80	
		f _{VCO_OUT} = 1000 MHz	-	0.95	1.20	

1. Based on test during characterization.

5.3.15 MIPI D-PHY regulator characteristics

The parameters given in [Table 54](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 54. DSI regulator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DD12DSI}	1.2 V internal voltage on V _{DD12DSI}	-	1.15	1.20	1.30	V
C _{EXT}	External capacitor on V _{CAPDSI}	-	1.1	2.2	3.3	μF
ESR	External Serial Resistor	-	0	25	600	mΩ
I _{DDDSIREG}	Regulator power consumption	-	100	120	125	μA
I _{DDDSI}	DSI system (regulator, PLL and D-PHY) current consumption on V _{DDDSI}	Ultra Low Power Mode (Reg. ON + PLL OFF)	-	290	600	μA
		Stop State (Reg. ON + PLL OFF)	-	290	600	
I _{DDDSILP}	DSI system current consumption on V _{DDDSI} in LP mode communication ⁽²⁾	10 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	mA
		20 MHz escape clock (Reg. ON + PLL OFF)	-	4.3	5.0	
I _{DDDSIHS}	DSI system (regulator, PLL and D-PHY) current consumption on V _{DDDSI} in HS mode communication ⁽³⁾	300 Mbps - 1 data lane (Reg. ON + PLL ON)	-	8.0	8.8	mA
		300 Mbps - 2data lane (Reg. ON + PLL ON)	-	11.4	12.5	
		500 Mbps - 1 data lane (Reg. ON + PLL ON)	-	13.5	14.7	
		500 Mbps - 2data lane (Reg. ON + PLL ON)	-	18.0	19.6	
	DSI system (regulator, PLL and D-PHY) current consumption on V _{DDDSI} in HS mode with CLK like payload	500 Mbps - 2data lane (Reg. ON + PLL ON)	-	21.4	23.3	
t _{WAKEUP}	Startup delay	C _{EXT} = 2.2 μF	-	110	-	μs
		C _{EXT} = 3.3 μF	-	-	160	
I _{INRUSH}	Inrush current on V _{DDDSI}	External capacitor load at start	-	60	200	mA

1. Based on test during characterization.

2. Values based on an average traffic in LP Command Mode.

3. Values based on an average traffic (3/4 HS traffic & 1/4 LP) in Video Mode.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 61. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Unit
				8/200 MHz	
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = 25 °C, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, over-drive ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	5	dBμV
			30 to 130 MHz	10	
			130 MHz to 1 GHz	18	
			1 GHz to 2 GHz	10	
			EMI Level	3.5	-
		V _{DD} = 3.6 V, T _A = 25 °C, TFBGA216 package, conforming to IEC61967-2 ART/L1-cache ON, over-drive ON, all peripheral clocks enabled, clock dithering enabled.	0.1 to 30 MHz	2	dBμV
			30 to 130 MHz	9	
			130 MHz to 1 GHz	14	
			1 GHz to 2 GHz	9	
			EMI Level	3	-

5.3.18 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/ESDA/JEDEC JS-001-2012 and ANSI/ESD S5.3.1-2009 standards.

Table 89. SAI characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{v(SD_B_ST)}$	Data output valid time	Slave transmitter (after enable edge) $2.7 \leq VDD \leq 3.6V$	-	12	ns
		Slave transmitter (after enable edge) $1.71 \leq VDD \leq 3.6V$	-	20	
$t_{h(SD_B_MT)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{v(SD_MT_A)}$	Data output valid time	Master transmitter (after enable edge) $2.7 \leq VDD \leq 3.6V$	-	15	
		Master transmitter (after enable edge) $1.71 \leq VDD \leq 3.6V$	-	20	
$t_{h(SD_A_MT)}$	Data output hold time	Master transmitter (after enable edge)	5	-	

1. Guaranteed by characterization results.
2. APB clock frequency must be at least twice SAI clock frequency.
3. With $F_S=192kHz$.

Figure 53. SAI master timing waveforms

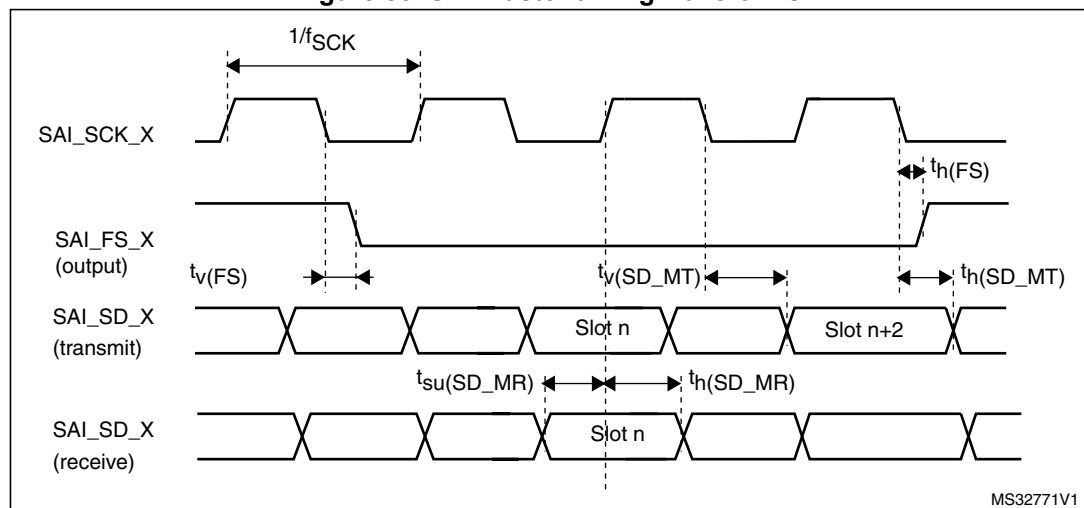
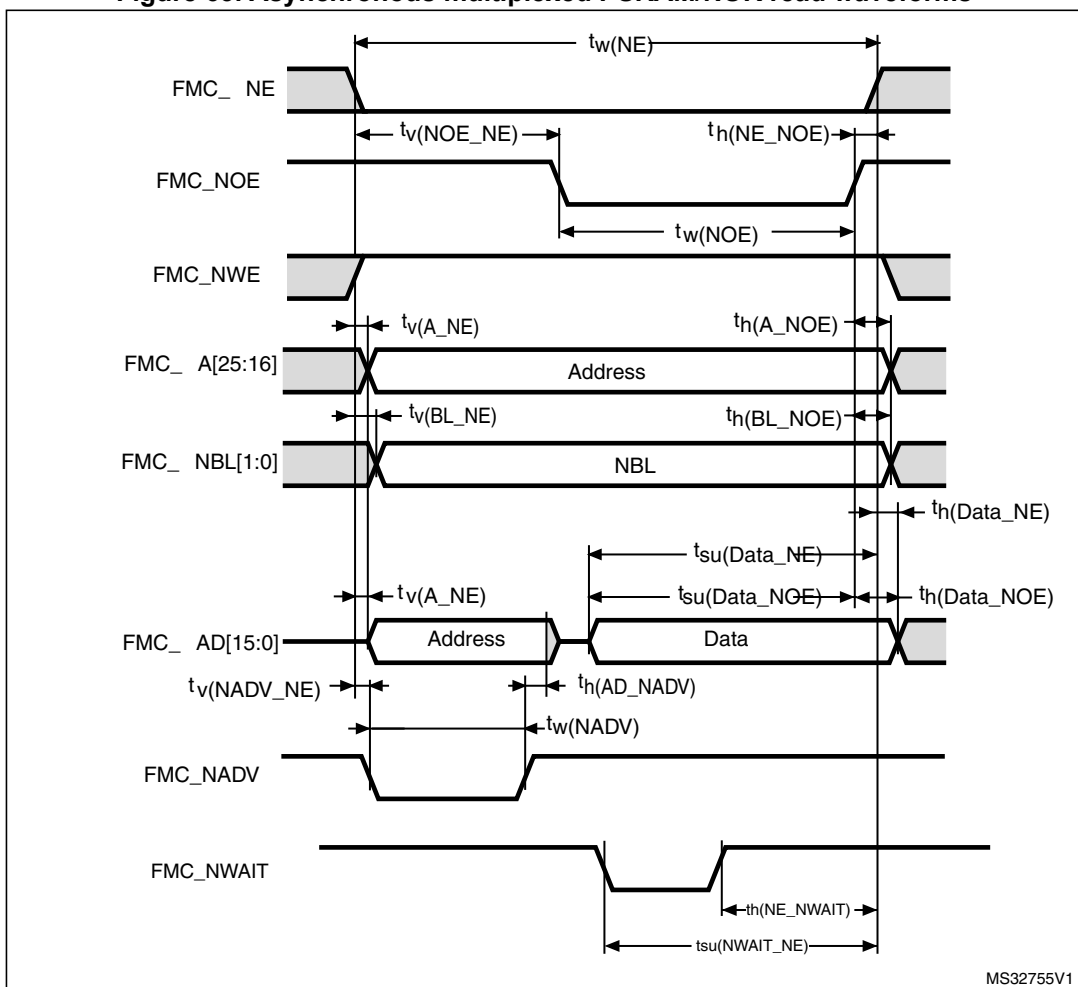


Table 103. Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK} - 1$	$8T_{HCLK} + 1$	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK} - 1.5$	$6T_{HCLK} + 0.5$	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK} - 1$	-	
$t_h(NE_NWAIT)$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK} + 2$	-	

1. Guaranteed by characterization results.

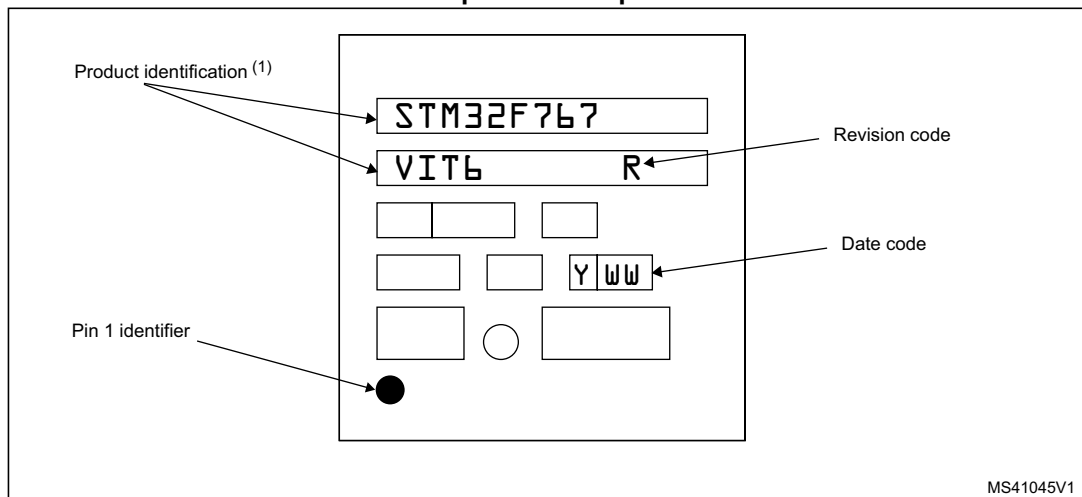
Figure 63. Asynchronous multiplexed PSRAM/NOR read waveforms

LQFP100 device making

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

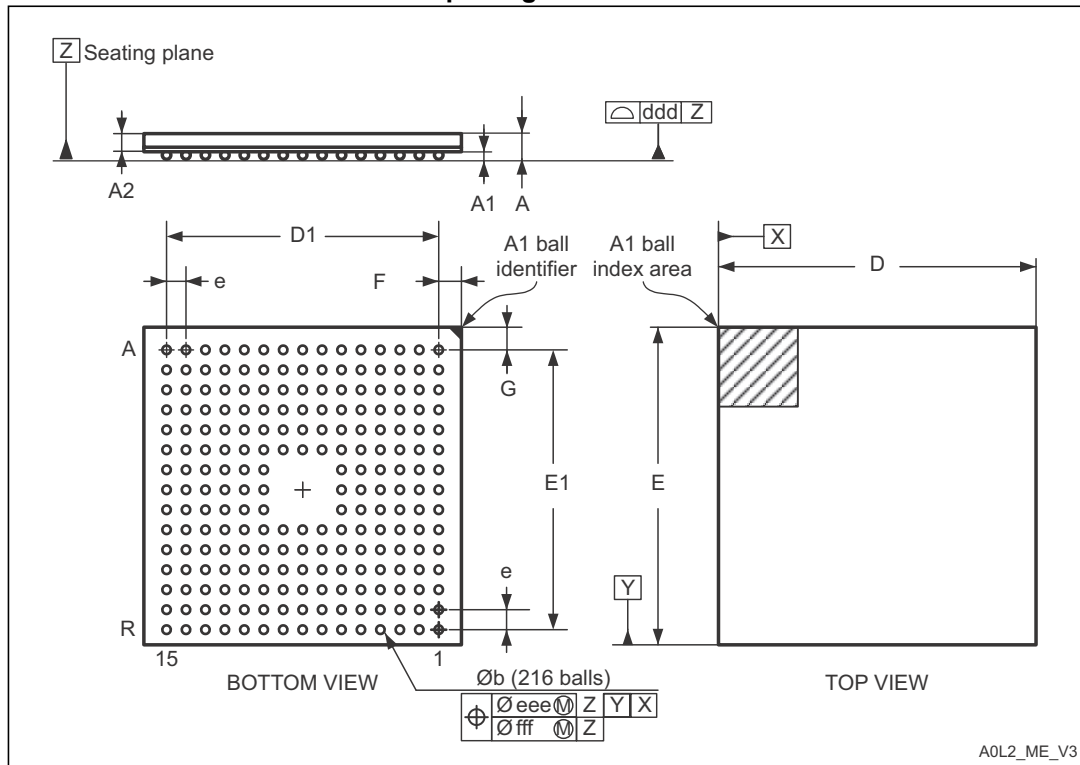
**Figure 85. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package
top view example**



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.7 TFBGA216, 13 x 13 x 0.8 mm thin fine-pitch ball grid array package information

Figure 101. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 133. TFBGA216, 13 × 13 × 0.8 mm thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.100	-	-	0.0433
A1	0.150	-	-	0.0059	-	-
A2	-	0.760	-	-	0.0299	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	12.850	13.000	13.150	0.5118	0.5118	0.5177
D1	-	11.200	-	-	0.4409	-
E	12.850	13.000	13.150	0.5118	0.5118	0.5177
E1	-	11.200	-	-	0.4409	-
e	-	0.800	-	-	0.0315	-
F	-	0.900	-	-	0.0354	-